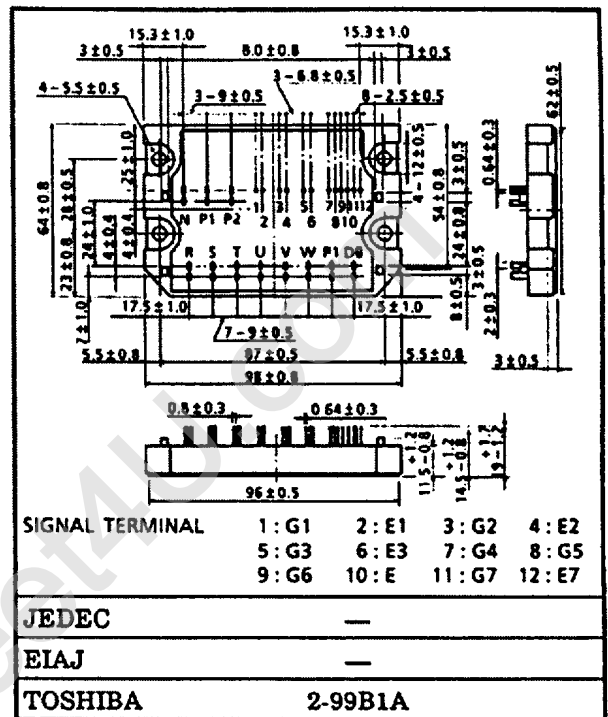


Unit in mm

High Power Switching Applications

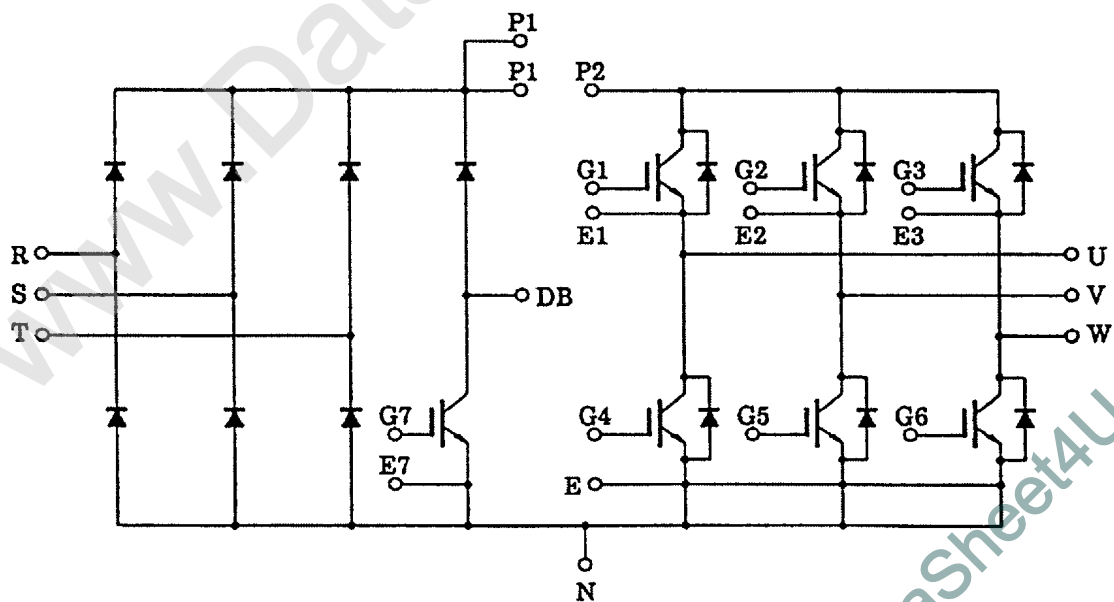
Motor Control Applications

- Integrates Inverter, Converter and Brake Power Circuits in One Package.
- Output (Inverter Stage)
 - : 3 ϕ 25A/1200V High Speed Type IGBT
 - $V_{CE(sat)}$ = 4.0V (Max.)
 - t_f = 0.40 μ s (Max.)
 - t_{rr} = 0.50 μ s (Max.)
- Input (Converter Stage)
 - : 3 ϕ 15A/1600V Silicon Rectifier
 - V_F = 1.20V (Max.)
- Brake Stage
 - : 8A/1200V IGBT & 8A/1200V FRD
- The Electrodes are Isolated from Case.



Weight : 245g

Equivalent Circuit



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Maximum Ratings (Ta = 25°C)

STAGE	CHARACTERISTIC		SYMBOL	RATINGS	UNIT	
Inverter	Collector-Emitter Voltage		V_{CES}	1200	V	
	Gate-Emitter Voltage		V_{GES}	±20	V	
	Collector Current	DC	I_C	25	A	
		1ms	I_{CP}	50	A	
	Forward Current	DC	I_F	25	A	
		1ms	I_{FM}	50	A	
Collector Power Dissipation (Tc = 25°C)			P_C	150	W	
Converter	Repetitive Peak Reverse Voltage		V_{RRM}	1600	V	
	Average Output Rectified Current		I_O	15	A	
	Peak One Cycle Surge Forward Current (50Hz, Non-Repetitive)		I_{FSM}	400	A	
Brake	IGBT	Collector-Emitter Voltage		V_{CES}	1200	V
		Gate-Emitter Voltage		V_{GES}	±20	V
		Collector Current	DC	I_C	8	A
			1ms	I_{CP}	16	A
	Collector Power Dissipation (Tc = 25°C)			P_C	80	W
	FRD	Repetitive Peak Reverse Voltage		V_{RRM}	1200	V
		Forward Current	DC	I_F	8	A
			1ms	I_{FM}	16	A
Module		Junction Temperature		T_j	150	°C
	Storage Temperature Range		T_{stg}	-40 ~ 125	°C	
	Isolation Voltage		V_{isol}	2500 (AC 1 minute)	V	
	Screw Torque		—	3	N·m	

Electrical Characteristics (Ta = 25°C)

a. Inverter Stage

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MX.	UNIT
Gate Leakage Current		I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	-	-	± 10	μA
Collector Cut-off Current		I_{CES}	$V_{CE} = 1200V, V_{GE} = 0$	-	-	1.0	mA
Gate-Emitter Cut-off Voltage		$V_{GE (off)}$	$I_C = 25mA, V_{CE} = 5V$	3.0	-	6.0	V
Collector-Emitter Saturation Voltage		$V_{CE (sat)}$	$I_C = 25A, V_{GE} = 15V$	-	3.00	4.00	V
Input Capacitance		C_{ies}	$V_{CE} = 10V, V_{GE} = 0$ $f = 1MHz$	-	3080	-	pF
Switching Time	Turn-on Delay Time	$t_{d(on)}$	Inductive Load $V_{CC} = 600V$ $I_C = 25A$ $V_{GE} = \pm 15V$ $R_G = 51\Omega$ (Note 1)	-	0.08	0.16	μs
	Rise Time	t_r		-	0.12	0.24	
	Turn-on Time	t_{on}		-	0.40	0.80	
	Turn-off Delay Time	$t_{d(off)}$		-	0.30	0.60	
	Fall Time	t_f		-	0.20	0.40	
	Turn-off Time	t_{off}		-	0.70	1.30	
Forward Voltage		V_F	$I_F = 25A, V_{GE} = 0$	-	2.00	2.50	V
Reverse Recovery Time		t_{rr}	$I_F = 25A, V_{GE} = -10V$ $di/dt = 100A/\mu s$	-	0.20	0.50	μs
Thermal Resistance		$R_{th(j-c)}$	Transistor	-	-	0.833	$^{\circ}C/W$
			Diode	-	-	1.30	

b. Converter Stage

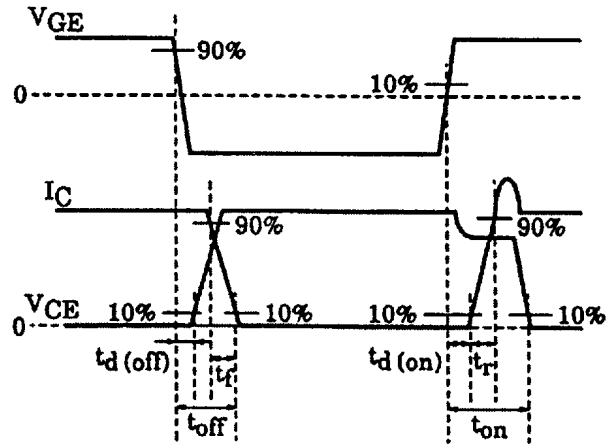
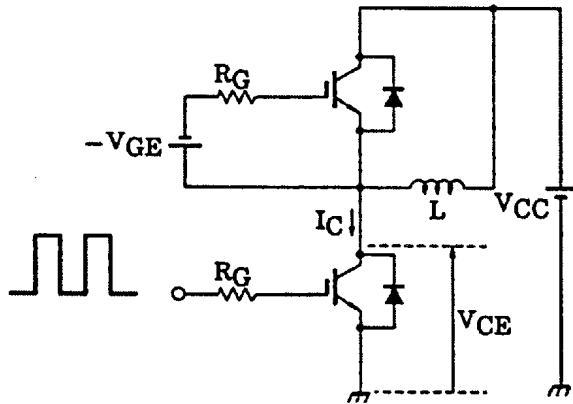
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MX.	UNIT
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM} = 1600V$	-	-	50	μA
Peak Forward Voltage	V_{FM}	$I_{FM} = 15A$	-	1.05	1.20	V
Peak One Cycle Surge Forward Current	I_{FSM}	50Hz Sine-half-wave	400	-	-	A
Thermal Resistance	$R_{th(j-c)}$		-	-	1.56	$^{\circ}C/W$

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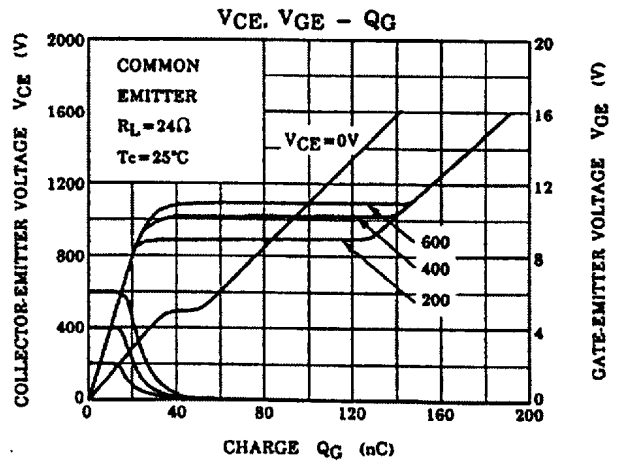
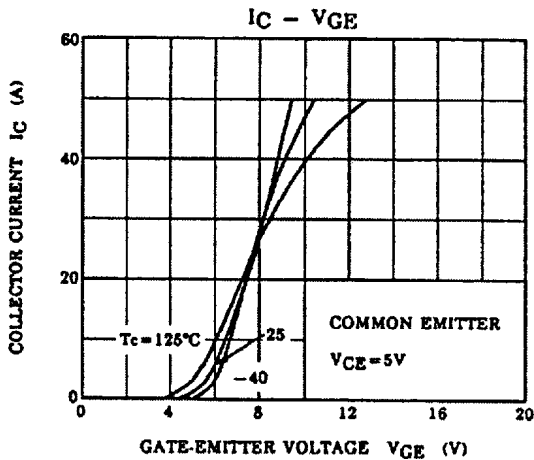
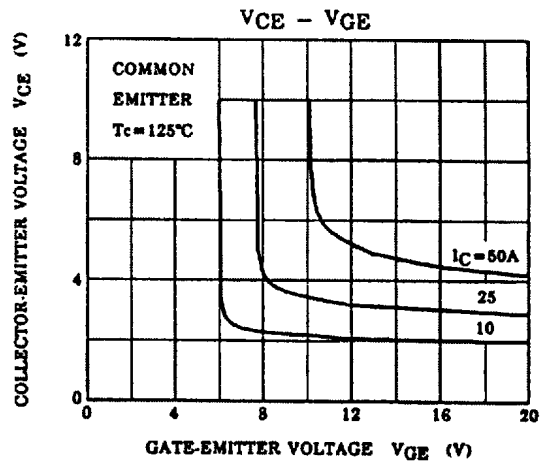
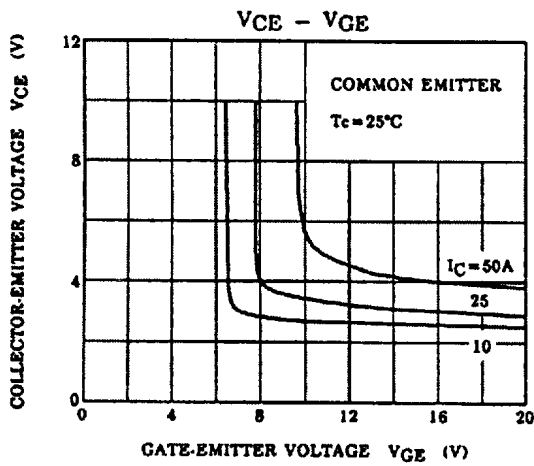
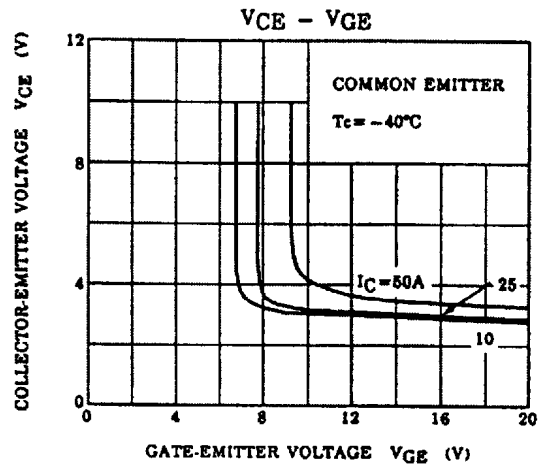
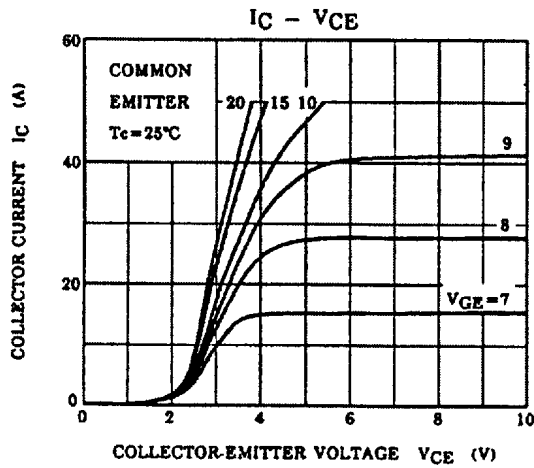
c. Brake Stage

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MX.	UNIT
Gate Leakage Current		I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	-	-	± 10	μA
Collector Cut-off Current		I_{CES}	$V_{CE} = 1200V, V_{GE} = 0$	-	-	1.0	mA
Repetitive Peak Reverse Current		I_{RRM}	$V_{RRM} = 1200V$	-	-	1.0	mA
Gate-Emitter Cut-off Voltage		$V_{GE(off)}$	$V_{CE} = 8mA, V_{CE} = 5V$	3.0	-	6.0	V
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 8A, V_{GE} = 15V$	-	3.00	4.00	V
Input Capacitance		C_{ies}	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	-	1000	-	pF
Switching Time	Turn-on Delay Time	$t_{d(on)}$	Inductive Load	-	0.08	0.16	μs
	Rise Time	t_r	$V_{CC} = 600V$	-	0.12	0.24	
	Turn-on Time	t_{on}	$I_C = 8A$	-	0.40	0.80	
	Turn-off Delay Time	$t_{d(off)}$	$V_{GE} = \pm 15V$	-	0.30	0.60	
	Fall Time	t_f	$R_G = 150\Omega$	-	0.30	0.50	
	Turn-off Time	t_{off}	(Note 1)	-	0.70	1.30	
Forward Voltage		V_F	$I_F = 8A, V_{GE} = 0$	-	1.20	2.50	V
Thermal Resistance		$R_{th(j-c)}$	Transistor	-	-	1.56	$^{\circ}C/W$
			Diode	-	-	1.80	

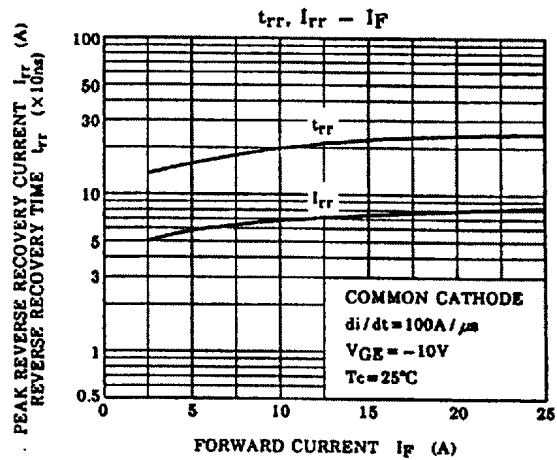
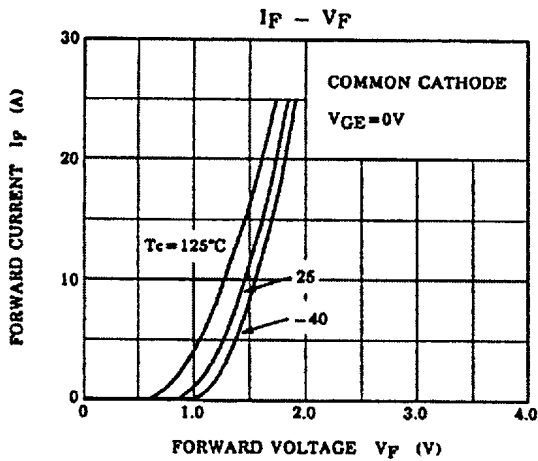
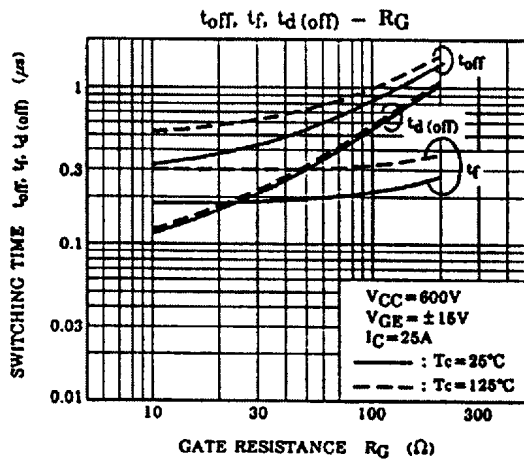
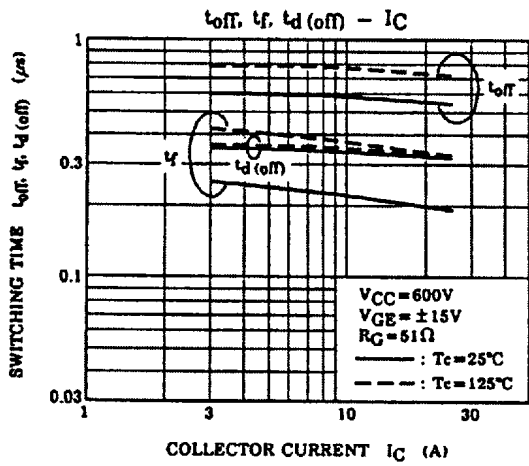
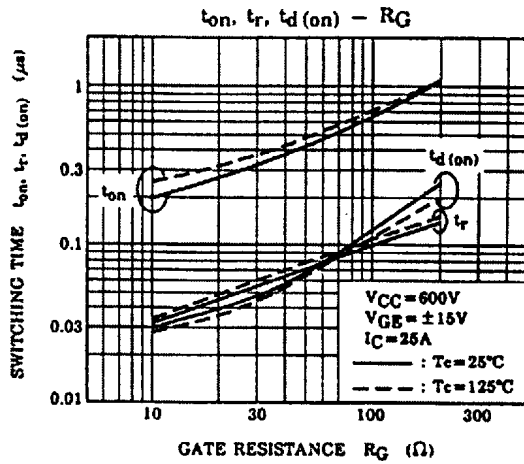
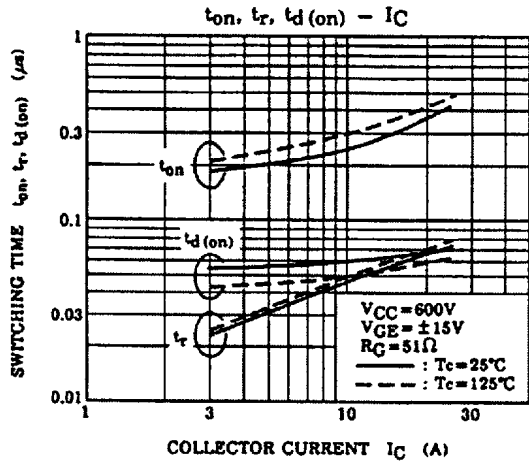
Note. 1 Switching Time Test Circuit & Timing Chart



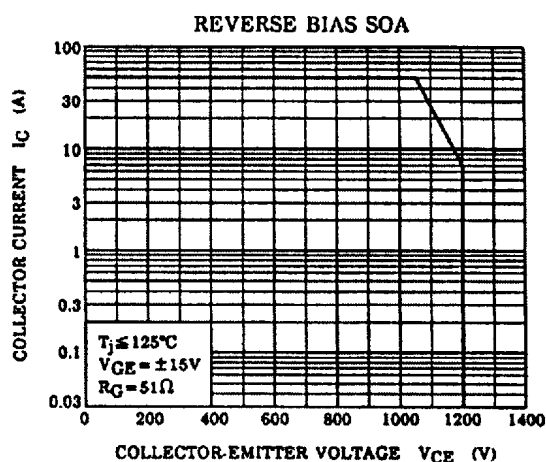
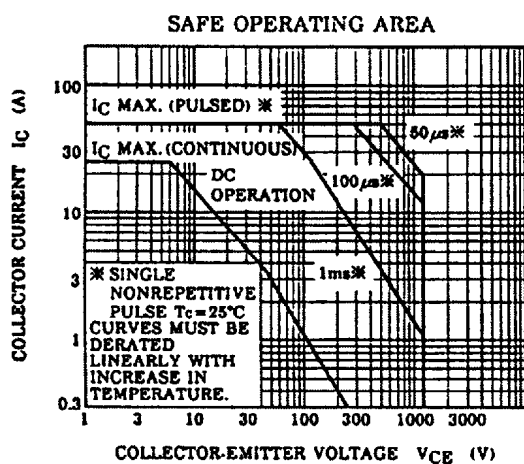
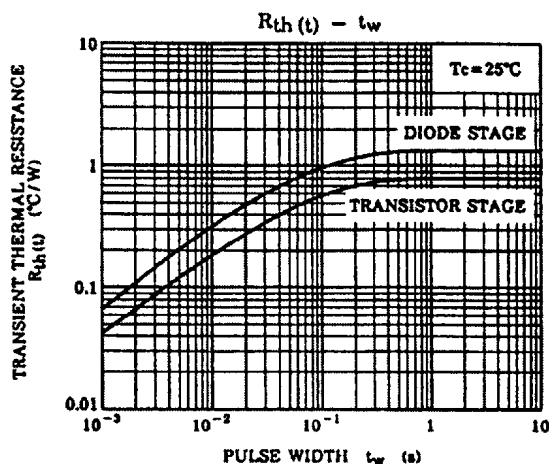
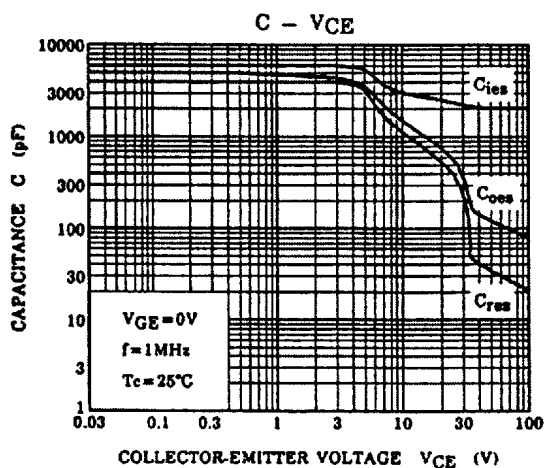
a. Inverter Stage



a. Inverter Stage

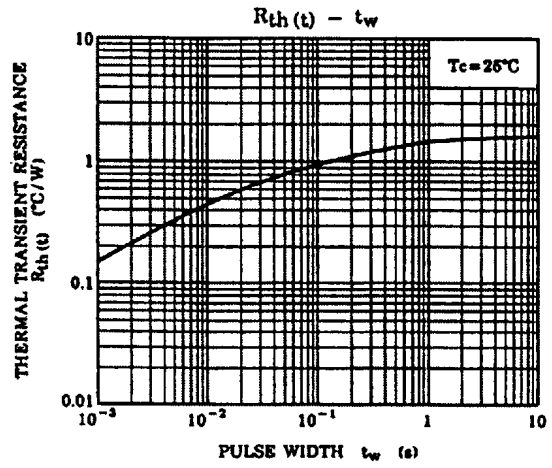
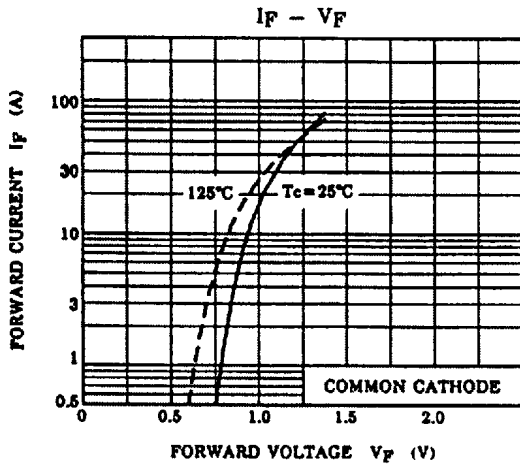


a. Inverter Stage

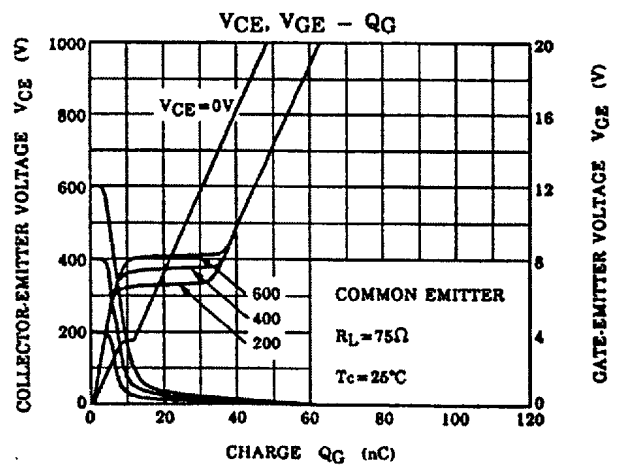
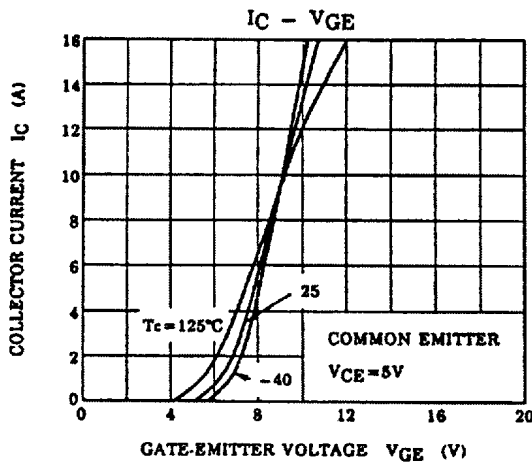
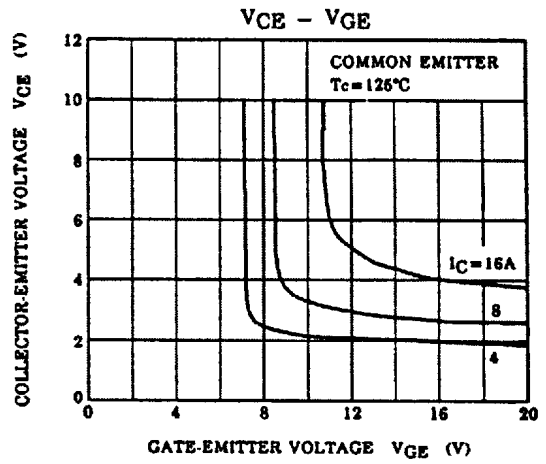
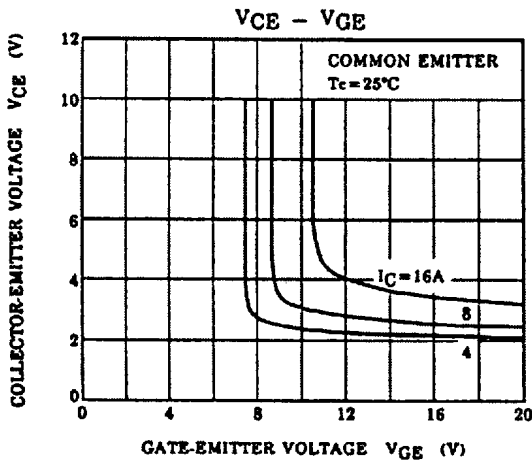
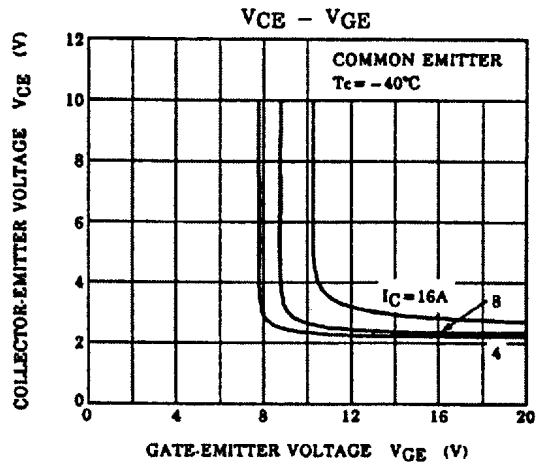
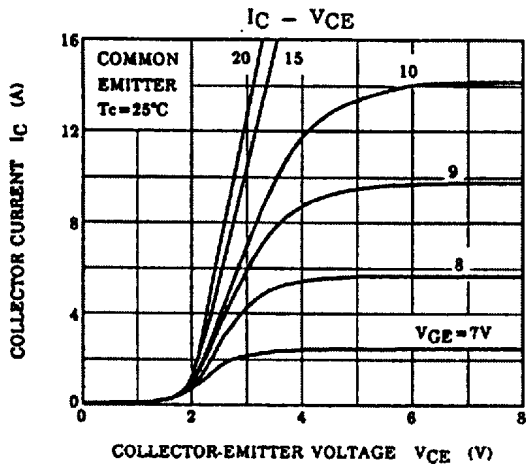


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b. Converter Stage

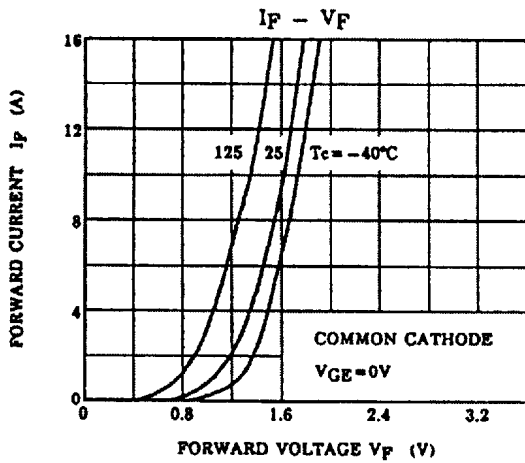
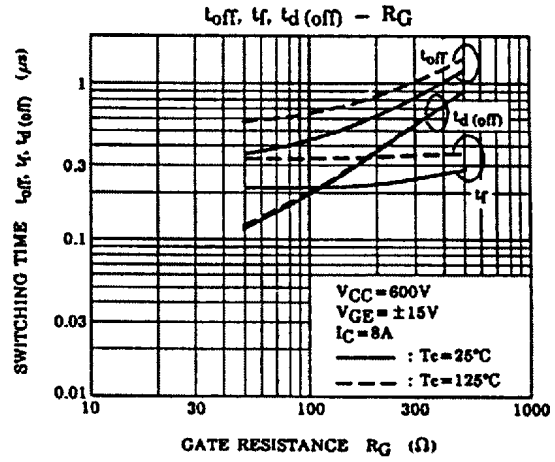
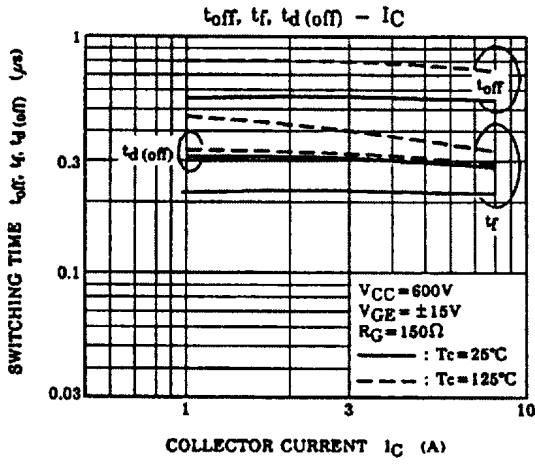
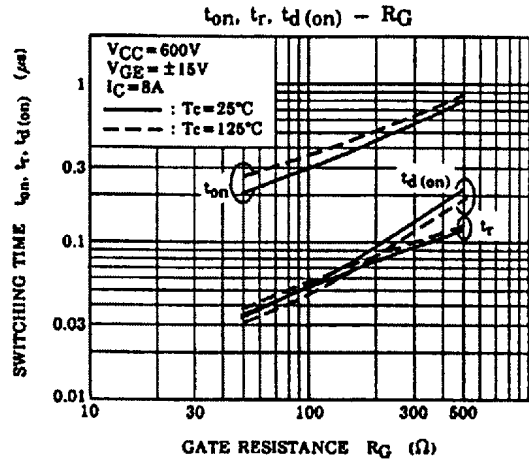
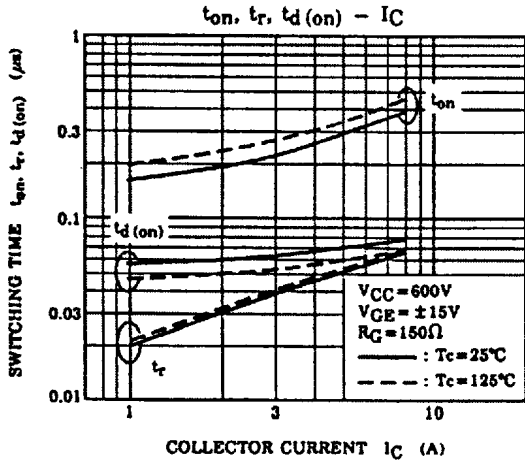


c. Brake Stage



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c. Brake Stage



c. Brake Stage

